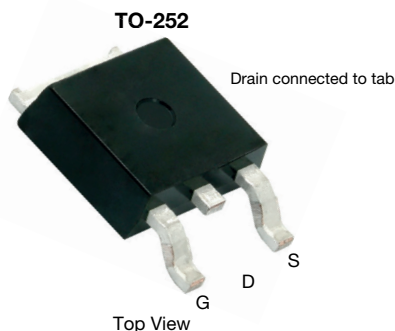


N-Channel 150 V (D-S) 175 °C MOSFET



FEATURES

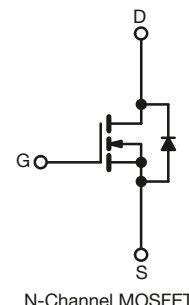
- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Boost converter
- LED backlighting
- Synchronous rectification
- Power supplies
- DC/AC inverter



PRODUCT SUMMARY

V _{DS} (V)	150
R _{DS(on)} max. (Ω) at V _{GS} = 10 V	0.0447
Q _g typ. (nC)	10.5
I _D (A)	42 ^d
Configuration	Single

ORDERING INFORMATION

Package	TO-252
Lead (Pb)-free and halogen-free	SUD80460E-GE3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V _{DS}	150	V
Gate-source voltage	V _{GS}	± 20	
Continuous drain current	I _D	42 ^d	A
		18.1	
Pulsed drain current (t = 100 μs)	I _{DM}	40	
Continuous source-drain diode current	I _S	42 ^d	
Single pulse avalanche current ^a	L = 0.1 mH I _{AS}	25	mJ
Single pulse avalanche energy ^a		31.25	
Maximum power dissipation	T _C = 25 °C P _D	65.2 ^b	W
		21.7 ^b	
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	MAXIMUM	UNIT
Maximum junction-to-ambient (PCB mount) ^c	R _{thJA}	50	°C/W
Maximum junction-to-case (drain)	Steady state R _{thJC}	2.3	

Notes

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).
- Package limited.



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	150	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2	-	4	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	250	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 150 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 150 V, V _{GS} = 0 V, T _J = 125 °C	-	-	150	
		V _{DS} = 150 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 8.3 A	-	0.0372	0.0447	Ω
Forward transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 8.3 A	-	11	-	S
Dynamic ^b						
Input capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz	-	560	-	pF
Output capacitance	C _{oss}		-	148	-	
Reverse transfer capacitance	C _{rss}		-	8	-	
Total gate charge	Q _g	V _{DS} = 75 V, V _{GS} = 10 V, I _D = 8.3 A	-	10.5	16	nC
Gate-source charge	Q _{gs}		-	2.7	-	
Gate-drain charge	Q _{gd}		-	3.1	-	
Gate resistance	R _g	f = 1 MHz	1.44	7.2	14.4	Ω
Turn-on delay time	t _{d(on)}	V _{DD} = 75 V, R _L = 10.7 Ω, I _D ≅ 7 A, V _{GEN} = 10 V, R _g = 1 Ω	-	8	16	ns
Rise time	t _r		-	20	30	
Turn-off delay time	t _{d(off)}		-	15	25	
Fall time	t _f		-	30	50	
Drain-Source Body Diode Characteristics						
Pulse diode forward current (t = 100 μs)	I _{SM}		-	-	42	A
Body diode voltage	V _{SD}	I _F = 7 A, V _{GS} = 0 V	-	0.85	1.5	V
Body diode reverse recovery time	t _{rr}	I _F = 7 A, di/dt = 100 A/μs	-	68	102	ns
Body diode reverse recovery charge	Q _{rr}		-	0.21	0.32	μC
Reverse recovery fall time	t _a		-	56	-	ns
Reverse recovery rise time	t _b		-	12	-	
Body diode peak reverse recovery charge	I _{RM(REC)}		-	5.5	10	A

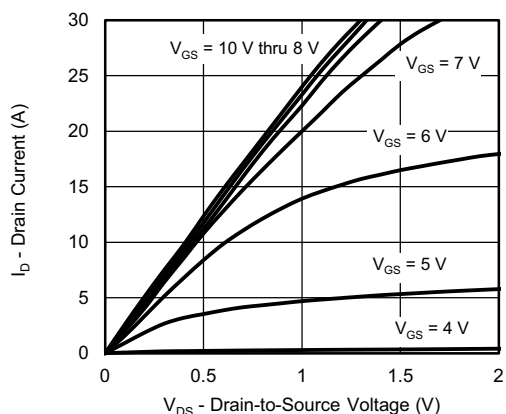
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

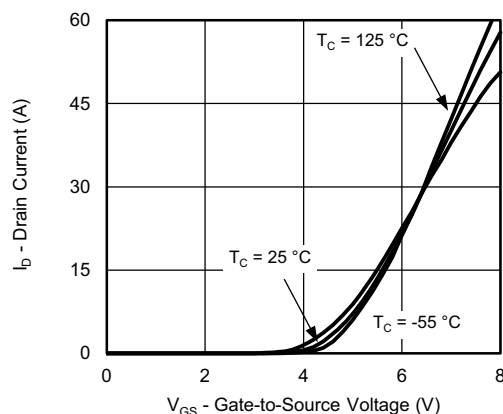
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



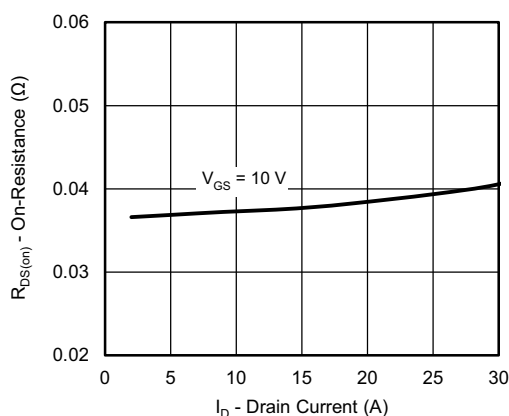
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



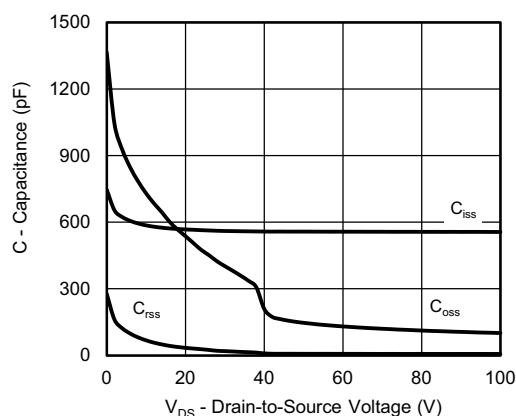
Output Characteristics



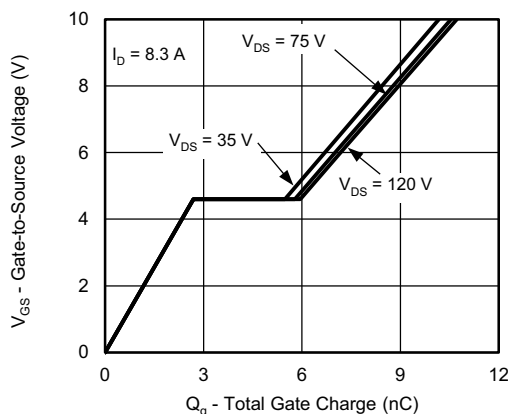
Transfer Characteristics



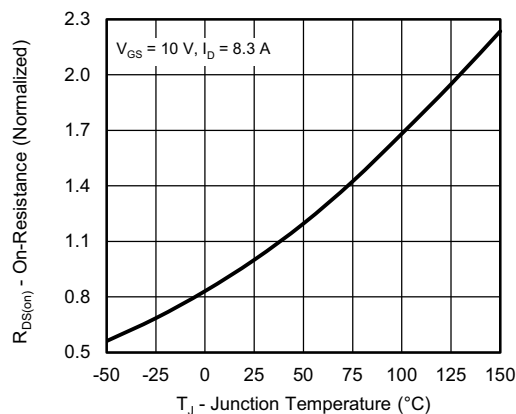
On-Resistance vs. Drain Current and Gate Voltage



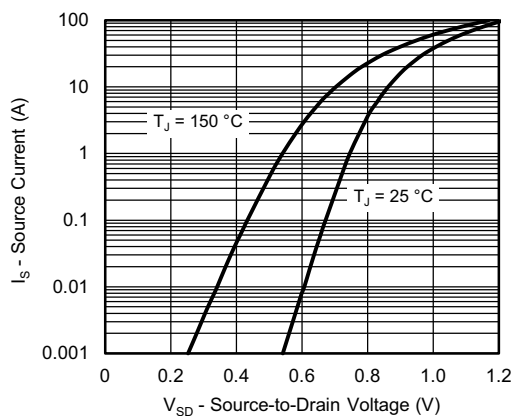
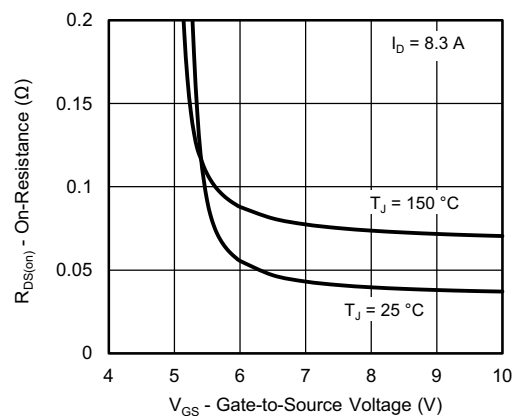
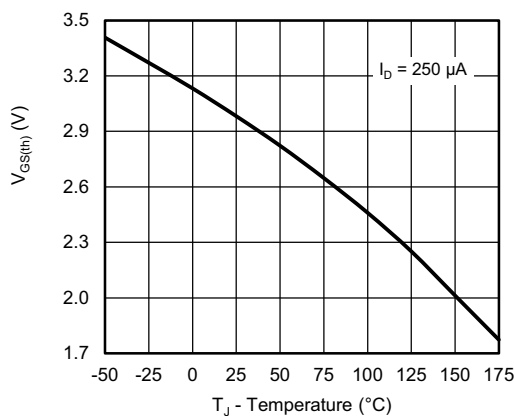
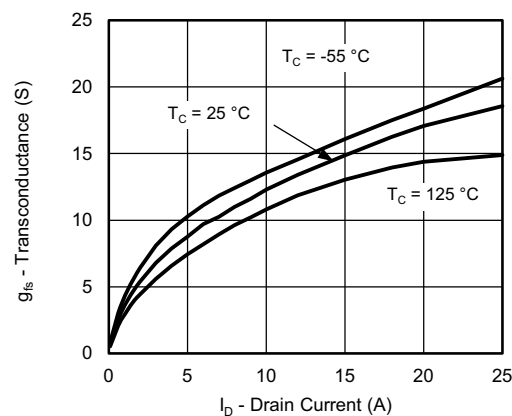
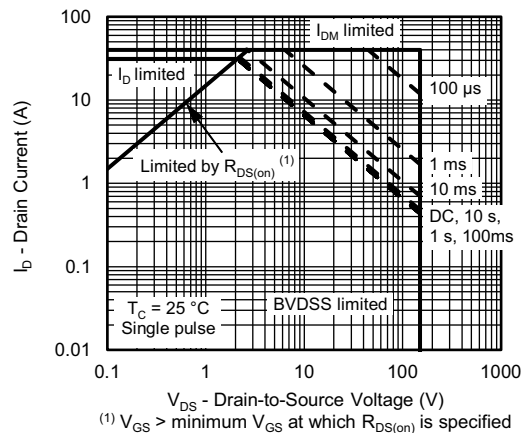
Capacitance

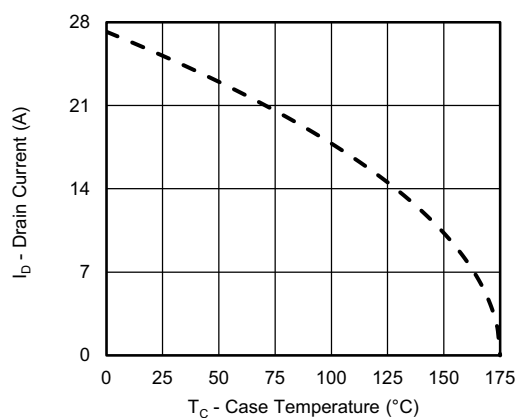
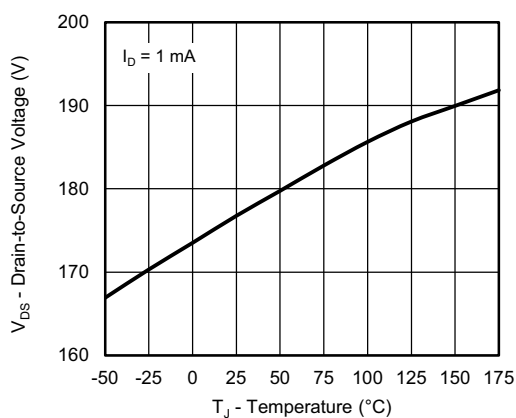
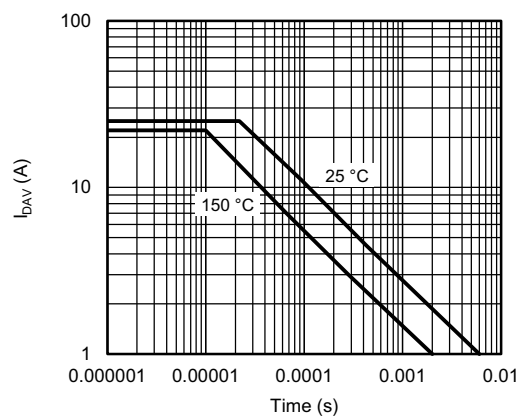


Gate Charge



On-Resistance vs. Junction Temperature

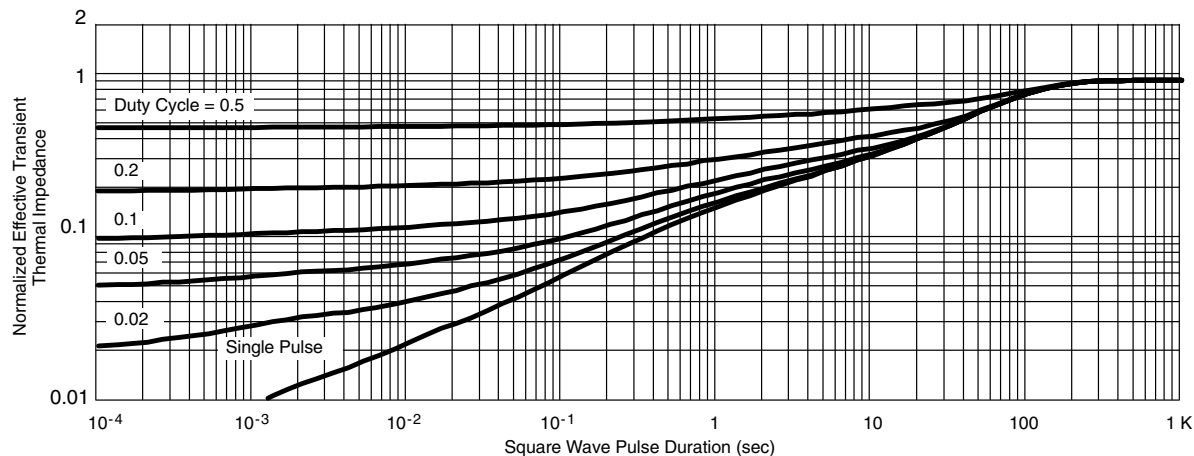
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Transconductance

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Drain Source Breakdown vs. Junction Temperature

 I_{DAV} vs. Time
Note

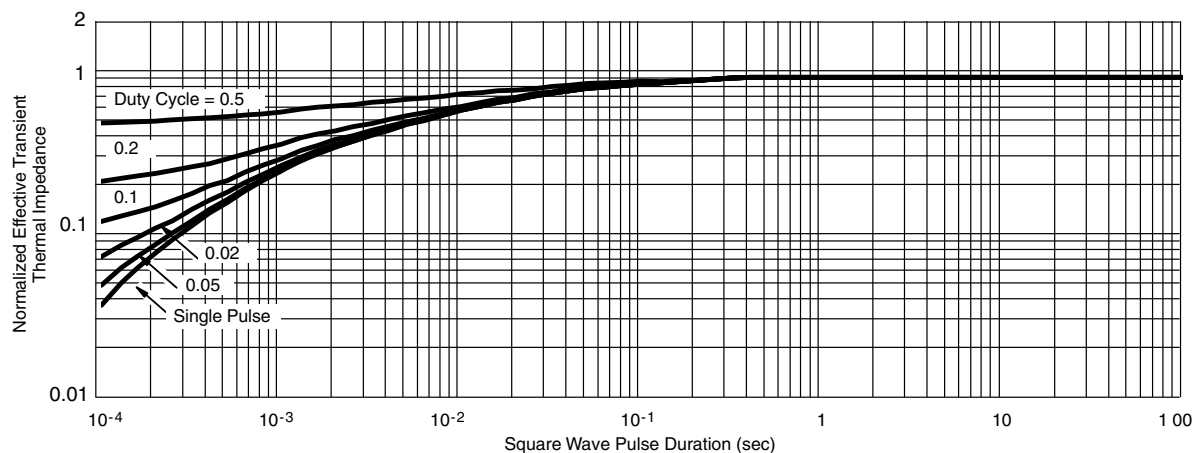
- a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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